**DHANALAKSHMI SRINIVASAN COLLEGE OF ENGINEERING**

 **AND TECHNOLOGY**

# DEPARTMENT OF ELECTRONICS AND COMMUNICATION ENGINEERING

**QUESTION BANK**

**Academic Year: 2018 – 2019 Odd Semester**

**Subject: EC8353 - ELECTRON DEVICES AND CIRCUITS**

# SEM/YEAR: III Semester/ II Year EEE

**QUESTION BANK**

SUBJECT : EC8353 - ELECTRON DEVICES AND CIRCUITS SEM/ YEAR : III / II YEAR EEE

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| **UNIT I - PN JUNCTION DEVICES** |
| PN junction diode –structure, operation and V-I characteristics, diffusion and transient capacitance -Rectifiers – Half Wave and Full Wave Rectifier,– Display devices- LED, Laser diodes- Zener diode characteristics-Zener Reverse characteristics – Zener as regulator |
| **PART - A** |
| **Q. No** | **Questions** | **BT Level** | **Domain** |
| 1. | Draw the symbol of the following devices PN Diode, Zener Diode, LED, and UJT. | BTL 1 | Remembering |
| 2. | What is a rectifier? Name its types. | BTL 1 | Remembering |
| 3. | Predict the diffusion capacitance fora silicon diode with a 10 mA forwardcurrent, if the charge carrier transit time is 60ns. | BTL 3 | Applying |
| 4. | How does the transition region width and contact potential across a PN junction vary with the applied bias voltage? | BTL 1 | Remembering |
| 5. | With suitable expression model transition capacitance and Diffusion capacitance? | BTL 3 | Applying |
| 6. | Construct the LASER Diode and give its applications. | BTL 3 | Applying |
| 7. | A full-wave rectifieruses two diodes, the internal resistance of each diode may be assumed constant at 20 Ω. The transformer R.M.S. secondary voltage from Centre tap to each end of secondary is 50 V and load resistance is 980 Ω. Evaluate : (i) The mean load current (ii) The R.M.S.value of load current | BTL ~~4~~ | Analyzing |
| 8. | List out the factors on which barrier potential depends. | BTL 1 | Remembering |
| 9. | Discuss the effect of temperature on reverse saturation current of a diode. | BTL6 | Creating |
| 10. | Outline transformer utilization factor and state its value for HWR andFWR. | BTL 2 | Understanding |
| 11. | Compare and contrast between P-N junction diode and Zener diode. | BTL 2 | Understanding |
| 12. | Assess the terms Knee voltage (VC) and Breakdown voltage (VB). | BTL 5 | Evaluating |
| 13. | Calculate the total power supplied to a 3½ digit LED display when it indicates 1999. A 5V supply is used and each LED has a 10 mA Current. | BTL 4 | Analyzing |
| 14. | State the mathematical equation which relates voltage applied across the PN junction diode and current flowing through it and list the PN diodeparameters. | BTL 1 | Remembering |
| 15. | Summarize the limiting values of PN Junction Diode. | BTL 2 | Understanding |
| 16. | A silicon diode has a saturation current of 7.5μA at room temperature.Estimate the saturation current at 400 ° K | BTL 6 | Creating |

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| 18. | Define Diode-resistance. | BTL 1 | Remembering |
| 19. | A Ge diode has a saturation current of 10μA at 300ᵒ K. Determine thesaturation current at 400ᵒK. | BTL 5 | Evaluating |
| 20. | Show the VI characteristics of Zener diode and Mention its applications. | BTL 2 | Understanding |
| **PART - B** | 17. | Distinguish between Zener Breakdown and Avalanche Breakdown | BTL 4 | Analyzing |
| 1. | With neat sketch compose the construction, operation and its characteristics of PN junction diode. Also list its advantages, disadvantages and its applications. (13) | BTL3 | Applying |
| 2. | Briefly enumerate the following1. Laser diodes (7)
2. Zener diode as a voltage regulator (6)
 | BTL1 | Remembering |
| 3. | 1. Summarize the effect of temperature on PN junction diode and draw its switching characteristics (8)
2. The reverse saturation of a silicon PN junction diode is 10μA. Infer the diode current for the forward bias voltage of 0.6V at 25ᵒ (5)
 | BTL 2 | Understanding |
| 4. | 1. Review the expression for current through the PN junction diode. (7)
2. Explain the V-I characteristics of Zener diode and Analyze between Avalanche and Zener Break downs? (6)
 | BTL 2 | Understanding |
| 5. | 1. Generalize the action of a full wave rectifier using diodes and give waveforms of input and output voltages. (6)
2. A FW diode rectifier has V1=100sinωt, RL=900Ω and Rf=100Ω. Come up with the peak and dc load current, DC load voltage, the peak instantaneous diode current, the PIV on the diode, AC input power, output power, Rectification efficiencyofthe FW rectifier. (7)
 | BTL 6 | Creating |
| 6. | 1. Determine the minimum and maximum values of the load resistance

of the Zener shunt regulator to meet the following specifications VS=24V, VZ=10V, iZMIN=3mA, IZMAX=50mA and RL=250Ω. (7)1. Show the circuit diagram of a half wave rectifier for producing a positive output voltage. Explain the circuit operation and sketch the

waveforms. (6) | BTL 1 | Remembering |
| 7. | 1. In what aspect is a LED different from a PN junction diode? Analyze the applications of LED. (7)
2. Illustrate the working of center tapped full wave rectifier with and without filter with neat diagrams. (6)
 | BTL 4 | Analyzing |
| 8. | Draw the circuit diagram and compose the working of full wave bridge rectifier with output filter and derive the expression of average output current, voltage, efficiency, ripple factor, PIV and TUF. (13) | BTL5 | Evaluating |
| 9. | Make use of a diagram recollect the working of Zener diode and its forward and reverse characteristics. Also distinguish between Avalanche and Zener break downs (13) | BTL2 | Understanding |
| 10. | 1. Describe the construction, operation and characteristics of LED. (7)
2. Examine how does Zener diode shunt voltage regulator operates. (6)
 | BTL 1 | Remembering |
| 11. | Derive ripple factor, PIV, efficiency and TUF of Bridge rectifier withcircuit diagram and input/output waveforms (13) | BTL4 | Analyzing |
| 12. | Examine the operation of half wave rectifierand derive FF, PF, RF, TUF,PIV and efficiency. (13) | BTL4 | Analyzing |

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| 13. | 1. Explain the VI characteristics of Zener diode. (6)
2. Derive the expression of the space charge or Transition capacitance of PN diode under reverse bias with neat diagram (7)
 | BTL 1 | Remembering |
| 14. | A bridge rectifier is supplied with 230V, 50Hz supply withstepdown ratioof 3:1 to a resistive load of 10kΩ. If the diode forward resistance is 75Ω while the transformer secondary resistance is 10Ω. Calculate the maximum and average values of current, dc output voltage and rms voltage, efficiency, ripple factor, peak factor, form factor, PIV and TUF.(13) | BTL 3 | Applying |
| **PART – C** |
| 1. | A germanium diode has a contact potential of 0.2volts while the concentration of accepted impurity atoms is 3x1020/m3. Calculate for a reverse bias of 0.1 volt, the width of the depletion region. If the reverse bias is increased to 10volt, calculate the new width of the depletion region. Assuming cross sectional area of the junction as 1mm2, Solve the transition capacitance values for both the cases. Assume εr=16 for germanium. (15) | BTL 6 | Creating |
| 2. | An AC supply of 220V, 50 Hz is applied to a HWR through a transformer of turn ratio 10:1. Determine (15)1. Maximum RMS load Voltage
2. Maximum RMS load current
3. Power delivered to the load
4. AC power input
5. Efficiency and ripple factor
6. PIV, ripple frequency, ripple voltage and ripple current.
 | BTL 5 | Evaluating |
| 3. | A 230 V, 50 Hz voltage is applied tothe primary of a 5:1 stepdown center- tapped transformer used in a FWR having a load of 900Ω. If the diode resistance and the secondary coil resistance together has a resistance of 100Ω evaluate, (15)1. DC voltage across the load
2. DC current flowing through the load
3. DC power delivered to the load
4. PIV across each diode
5. Ripple voltage and its frequency
 | BTL 5 | Evaluating |
| 4. | 1. A 5.0V stabilized power supply is required to be produced from a

12V DC power supply input source. The maximum power rating PZ of the Zener diode is 2W. Using the Zener regulator circuit below calculate: (8)* 1. The maximum current flowing through the Zener diode.
	2. The minimum value of the series resistor, RS
 | BTL6 | Creating |

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|  | 1. The load current IL if a load resistor of 1kΩ is connected across

the Zener diode.1. The Zener current IZ at full load.
2. Consider the characteristic curve fora Zener diode shown below (7)
	1. What is the current when the diode has a forward bias of 0.8 V?
	2. What is the breakdown voltage of this diode?
	3. What is the power dissipated in this diode when it carries a reverse current of 100 mA?
	4. Describe how this diode could be used to provide a steady voltage of 25 V across a load from an unregulated DC supply.
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| **UNIT II - TRANSISTORS AND THYRISTORS** |
| BJT, JFET, MOSFET- structure, operation, characteristics and Biasing UJT, Thyristor and IGBT -Structureand characteristics. |
| **PART - A** |
| **Q. No** | **Questions** | **BT Level** | **Domain** |
| 1. | State Base width modulation in transistor? | BTL 1 | Remembering |
| 2. | Review “Thermal runaway” in transistors and mention how it can be avoided. | BTL 2 | Understanding |
| 3. | A BJT has a base current of 200μA. Determine the collector currentand β. | BTL 5 | Evaluating |
| 4. | Draw the transfer and drain characteristic curves of JFET | BTL 1 | Remembering |
| 5. | Inspect why it is necessary to stabilize the operating point of transistor. | BTL 4 | Analyzing |
| 6. | In an N-channel JFET IDSS=20 mA and VP= -6V. Estimate the draincurrent when VGS= -3V. | BTL 5 | Evaluating |
| 7. | Differentiate between JFET and MOSFET. | BTL 4 | Analyzing |
| 8. | Make use of the values of transistor has β=150, find the collector and base current if IE= 10mA | BTL 1 | Remembering |
| 9. | Predict the dc current gain (DC & DC) and the emitter current IE for atransistor where IB = 50 A and IC = 3.65 mA. | BTL 6 | Creating |
| 10. | Express how an FET is used as a voltage variable resistor. | BTL 2 | Understanding |
| 11. | Interpret an intrinsic standoff ratio of UJT and draw its equivalentcircuits. | BTL 2 | Understanding |
| 12. | Discuss about thyristor and mention their types. | BTL 6 | Creating |

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| 13. | List out the different methods to turn on the thyristor? | BTL 1 | Remembering |
| 14. | An SCR in a circuit is subjected to a 50 A surge that lasts for 12 ms. Discover whether or not this surge will destroy the device. Given thatcircuit fusing rating is 90 A2 s. | BTL 3 | Applying |
| 15. | Define the terms Firing angle and Conduction angle of an SCR. | BTL 1 | Remembering |
| 16. | A 220Ω resistor is connected in series with the gate of an SCR The gate current required to fire the SCR is 7mA. What is the input voltage (Vin) required to fire the SCR? | BTL 1 | Remembering |
| 17. | Compare the characteristics of BJT, MOSFET and IGBT. | BTL 4 | Analyzing |
| 18. | Interpret the terms latching current & holding current. | BTL 3 | Applying |
| 19. | Show how an SCR can be triggered ON by the application of a pulse tothe gate terminal. | BTL 2 | Understanding |
| 20. | Write the difference between TRIAC and DIAC. | BTL 3 | Applying |

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|  | c) If VCC is decreased until the SCR opens, what is the value ofVCC? (8)

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| **PART - B** |
| 1. | Explain BJT Common Base configuration, with a neat diagram. Explainthe common base input and output characteristics with necessary graphs.(13) | BTL 2 | Understanding |
| 2. | Elaborate the construction and operation of NPN transistor with neatsketch. Also comment on the characteristics of NPN transistor. (13) | BTL 6 | Creating |
| 3. | 1. Summarize the input and output characteristics of an Emitter Follower. (7)
2. Compare and contrast between CE, CB and CC configurations. (6)
 | BTL 2 | Understanding |
| 4. | With neat diagram explain the working of Enhancement MOSFET &Depletion MOSFET withits necessary characteristics curve. (13) | BTL 3 | Applying |
| 5. | 1. Illustrate Early effect with relevant expressions and diagram. (6)
2. Demonstrate the input and output characteristics of CE configuration. (7)
 | BTL 3 | Applying |
| 6. | 1. Outline the hybrid model of BJT and derive the important parameters. (7)
2. Model and explain the typical shape of drain characteristics of JFET for VGS=0 with indication of four region clearly. (6)
 | BTL4 | Analyzing |
| 7. | 1. Enumerate the selection of Q point for transistor bias circuit and

discuss the limitations on the output voltage swing. (7)1. Show the cross section diagram of an N type enhancement mode MOSFET. Briefly explain its operation. (6)
 | BTL 2 | Understanding |
| 8. | Describe the construction and working of UJT with its equivalent circuitand VI characteristics. (13) | BTL1 | Remembering |
| 9. | Draw and explain the construction, operation and V-I characteristics ofSCR. (13) | BTL1 | Remembering |
| 10. | 1. Analyze the structure and operation of Insulated Gate Bipolar Transistor. (7)
2. Distinguishbetween MOSFET and IGBT. (6)
 | BTL4 | Analyzing |
| 11. | 1. Differentiate between SCR and UJT. (5)
2. The SCR of below figure has gate trigger voltage VT = 0.7V, gate trigger current IT = 7 mA and holding current IH = 6 mA. Calculate:
	1. The output voltage when the SCR is off?
	2. The input voltage that triggers the SCR?
 | BTL4 | Analyzing |

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| 12. | 1. The operation of UJT as a relaxation oscillator and derive its frequency of oscillation. (7)
2. Mention the advantages & applications of UJT. (6)
 | BTL 5 | Evaluating |
| 13. | 1. Outline the basic construction, operation and V-I characteristics of

DIAC. (7)1. Show the four layer construction, two transistor equivalent circuit of

an SCR and explainthe device operation in detail. (6) | BTL 1 | Remembering |
| 14. | 1. What is an IGBT? Draw the structure and equivalent model of an IGBT explain in detail with switching characteristics. (7)
2. Write in detail about the operation of TRIAC. (6)
 | BTL1 | Remembering |

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| **PART - C** |
| 1. | Design a voltage divider bias circuit fortransistor to establishthe quiscent point at VCE=12V, IC=1.5mA, stability factor S≤3, β = 50, VBE=0.7V,VCC=22.5V and RC=5.6kΩ. (15) | BTL 6 | Creating |
| 2. | Draw d.c load line and a.c load line for the following transistor configuration. Obtainthe operating point. (15) | BTL 6 | Creating |
| 3. | 1. For an n-channel silicon FET with a=3x10-4 cm and Nd=1015 electrons/cm-3. Evaluate (a) pinch off voltage (b) the channel half width for VGS= 0.5Vp. (5)
2. In biasing with feedback resistor method, a silicon transistor with

feedback resistor is used. The operating point is 7V, 1mA and VCC=12V. | BTL 5 | Evaluating |
|  | Assume β=100. Determine the value of RB, Stability factor and the newoperation point if β=50 and all other circuit values for the same.(10) |  |  |
| **4.** | The reverse leakage current of the transistor when connected in CB configuration is 0.2 mA and it is 18 μA when the same transistor is connected in CE configuration. Determine αdc & βdc of the transistor. Assume IB =30mA. (15) | **BTL 5** | **Evaluating** |

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| **UNIT III - AMPLIFIERS** |
| BJT small signal model – Analysis of CE, CB, CC amplifiers- Gain and frequency response – MOSFET small signal model– Analysis of CS and Source follower – Gain and frequency response-High frequency analysis. |
| **PART - A** |
| **Q. No** | **Questions** | **BT Level** | **Domain** |
| 1. | Sketch the hybrid model of BJT in CE and CB configuration. | BTL 1 | Remembering |
| 2. | Write about amplifiers and mention its applications. | BTL 1 | Remembering |
| 3. | Model the small signal equivalent circuit of a CS JFET. | BTL 3 | Applying |
| 4. | In a common base connection, current amplification factor is 0.9. If theemitter current is 1mA, find the value of base current. | BTL5 | Evaluating |
| 5. | Analyze the expressions for the h-parameters. | BTL 4 | Analyzing |
| 6. | For an amplifier, midband gain =100 and lower cut-off frequency is 1 kHz. Estimate the gain of an amplifier at frequency of 20Hz. | BTL 6 | Creating |
| 7. | Discuss the significance of coupling and bypass capacitor on bandwidth of amplifiers | BTL 2 | Understanding |
| 8. | Express the term bandwidth and gain bandwidth product. | BTL 1 | Remembering |
| 9. | Draw the DC equivalent circuit of an amplifier. | BTL 1 | Remembering |
| 10. | A common emitter amplifier has an input resistance 2.5kΩ and voltagegain of 200.If the input signal voltage is 5mV. Find the base current of the amplifier. | BTL5 | Evaluating |
| 11. | Point out why CE configuration is preferred over CB configuration. | BTL 4 | Analyzing |
| 12. | Outline the procedure to draw the AC equivalent of a network | BTL 2 | Understanding |
| 13. | Identify the reason for fall in gain at low and high frequencies in anamplifier. | BTL 3 | Applying |
| 14. | State Miller’s theorem. | BTL 1 | Remembering |
| 15. | When transistoracts as a switch, inwhich region of output characteristicsit is operated? | BTL 4 | Analyzing |
| 16. | Examine the features of Source follower. | BTL 3 | Applying |
| 17. | When VGS of the FET changes from -3.1V to 3V the drain currentchanges from 1 mA to 1.3mA Calculate the value of transconductance. | BTL 6 | Creating |
| 18. | Define transconductance of MOSFET. | BTL 1 | Remembering |
| 19. | Show the frequency response curve of an amplifier and what does 3 dB frequency denotes. | BTL 2 | Understanding |
| 20. | Compare the performance of CE,CB,CC amplifier configurations | BTL 2 | Understanding |
| **PART - B** |
| 1. | Illustrate the h-parameter model of a BJT-CE amplifier and derive the equations for voltage gain, current gain, input impedance and outputimpedance. (13) | BTL 2 | Understanding |
|  **2.** | Describe about small signal MOSFET amplifiers (NMOS) and obtaintheexpression for the transconductance. (13) |  **BTL1** | **Remembering** |
|  **3.** | Demonstrate the mid band analysis of single stage CE, CB and CC amplifiers. (13) |  **BTL3** | **Applying** |
|  **4.** | (i) Derive the expression for the voltage gain of CS amplifier. (5) (ii)Calculate the input capacitance limited cut-off frequency for the following circuit when operated as a CS circuit with RS by-passed. Assume that there is no additional stray capacitance at the input terminals and that the FET has the following parameters. . 𝐶𝑟𝑠𝑠 =1𝑝𝐹, 𝐶𝑖𝑠𝑠 = 5𝑝𝐹, 𝑌𝑓𝑠 = 2500𝜇𝑆 𝑎𝑛 𝑜𝑠 = 75𝜇𝑆. (8) |  **BTL3** | **Applying** |

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| 5. | 1. Discuss the factors involved in Ic, Rc and RE for a single stage common emitter BJT amplifiercircuit, usingvoltage divider bias. (5)
2. A CC amplifier shown in below figure has VCC=15 V, RB=75kΩ and RE=910Ω The β of the silicon transistor is 100 and the load resistor is 600Ω. Estimate Rin and Av. (8)
 | BTL6 | Creating |
| 6. | Draw the circuit diagram of a common drain MOSFET amplifier. Derivethe expression for its voltage gain, input resistance and output resistance.(13) | BTL 5 | Evaluating |
| 7. | Analyze the operation of CB amplifier and derive the expression for hparameters of the same. Also derive the expression for gain, input impedance and output impedance of CB amplifier. (13) | BTL4 | Analyzing |
| 8. | (i) | Explain about CS amplifier and derive the expression for gain, input impedance and output impedance and also draw its small Signal equivalent circuit. (ii) Express the equation for calculating the value of the source bypasscapacitor for a single stage common source amplifier using voltage divider bias using high frequency equivalent circuit. (6) (7) | BTL 2 | Understanding |

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|  | (ii) | Express the equation for calculating the value of the source bypasscapacitor for a single stage common source amplifier using voltage divider bias using high frequency equivalent circuit. (6) |  |  |

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| 5. | 1. Discuss the factors involved in Ic, Rc and RE for a single stage common emitter BJT amplifiercircuit, usingvoltage divider bias. (5)
2. A CC amplifier shown in below figure has VCC=15 V, RB=75kΩ and RE=910Ω The β of the silicon transistor is 100 and the load resistor is 600Ω. Estimate Rin and Av. (8)
 | BTL6 | Creating |
| 6. | Draw the circuit diagram of a common drain MOSFET amplifier. Derivethe expression for its voltage gain, input resistance and output resistance.(13) | BTL 5 | Evaluating |
| 7. | Analyze the operation of CB amplifier and derive the expression for hparameters of the same. Also derive the expression for gain, input impedance and output impedance of CB amplifier. (13) | BTL4 | Analyzing |
| 8. | (i) | Explain about CS amplifier and derive the expression for gain, input impedance and output impedance and also draw its small Signal equivalent circuit. (7) | BTL 2 | Understanding |

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|  | (ii) | Express the equation for calculating the value of the source bypasscapacitor for a single stage common source amplifier using voltage divider bias using high frequency equivalent circuit. (6) |  |  |
| 9. | The hybrid parameters of a transistor used as an amplifier in the CEconfiguration are hie = 800Ω, hfe = 46, hoe = 80 × 10-6 and hre = 5.4× 10-4. If RL = 5kΩ and Rs =500Ω. Find Ai, Ri , Av, Ro. (13) | BTL1 | Remembering |
| 10. | 1. Inspect the high frequency response of FET and derive the expression for lower cut off frequency and upper cut off frequency.

(9)1. The data sheet of an enhancement MOSFET gives ID(min) = 500mA at VGS = 10V and VGS(th) = 1V. Find the drain current for VGB = 5V.

(4) | BTL4 | Analyzing |
| 11. | 1. Demonstrate the low frequency analysis of BJT and also determine the effect of Cs, Cc & Cc on the low frequency response of BJT. (7)
2. Summarize the high frequency analysis of common source amplifier.

(6) | BTL 2 | Understanding |
| 12. | Explain about CC amplifier and derive the expression for h parametersof the same. Also derive the expression for gain, input impedance and output impedance of CC amplifier. (13) | BTL4 | Analyzing |
| 13. | Determine the mid-band gain and bandwidth of a CE amplifier shown in the figure. Assume lower cutoff frequency is 100Hz . Let hfe =β =100, Cbe = 4pF , Cbc=0.2pF and VA = ∞. (13) | BTL1 | Remembering |
| 14. | 1. Show the low frequency h-equivalent model of a transistor amplifier operating in CE mode and write why this circuit is not valid for high frequencies. (8)
2. Define the transconductance of BJT in the CE mode. How it is related to h parameters. (5)
 | BTL1 | Remembering |
| **PART – C** |
| 1. | (i) Determine the mid-band gain, upper cutoff frequency of a common source amplifier fed with the signal having internal resistance Rsig = 100kΩ. The amplifier has Rg = 4.7MΩ, RD = RL = 15kΩ, gm = 1mA /V, ro =150kΩ, Cgs =1pF and Cgd = 0.4pF. (8) | BTL5 | Evaluating |

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|  | (ii) For CS amplifier, the operating point is defined by VGSQ=-2.5V, VP=-6V & IdQ=2.5mA with IDSS=8mA. Also RG=1MΩ,RS=1KΩ,RD=2.2kΩ and VDD=15V. Calculategm, rd, Zi, ZO & AV. (7) |  |  |
| 2. | For a CB amplifier driven by voltage source of internal resistance Rs=1200Ω. The load impedance is resistor RL=1000Ω. The h parameters are hib=22Ω,hcb=3x10-4, hfb= -0.98 and hob=0.5A/V. Estimatethe current gain Ai, Input impedance Ri, voltage gain Av, overall current gain Ais, overall voltage gain Avs and output impedance Zo. (15) | BTL6 | Creating |
| 3. | The hybrid parameters for CE amplifier are hie = 1000 Ω , hfe = 150 , hre = 1.2 x10-4 , hoe = 2.5 x 10-6 mho. The transistor has a load resistance of 10kΩincollectorand supplied from signal source of 1k Ω. Deduce the values of input impedance, output impedance, current gain and voltage gain. (15) | BTL6 | Creating |
| 4. | The following figure shows a common emitter amplifier. Determine the input resistance, ac load resistance, voltage gain and output voltage. (15) | BTL5 | Evaluating |

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| **UNIT IV - MULTISTAGE AMPLIFIERS AND DIFFERENTIAL AMPLIFIER** |
| BIMOS cascade amplifier, Differential amplifier – Common mode and Difference mode analysis – FET input stages – Single tuned amplifiers – Gain and frequency response – Neutralization methods, power amplifiers – Types (Qualitative analysis). |
| **PART – A** |
| **Q.No** | **Questions** | **BT Level** | **Domain** |
| 1. | What are cascaded amplifiers? Mention the need for cascading the amplifiers. | BTL 1 | Remembering |
| 2. | A tuned circuit has a resonant frequency of 1600kHz and a bandwidth of 10kHz.Calculate the value of the Q factor . | BTL 3 | Applying |

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| 3. | Analyze how the differential amplifier can be used as an emitter coupledphase inverter | BTL 4 | Analyzing |
| 4. | Discuss the need for neutralization. | BTL 6 | Creating |
| 5. | A multistage amplifier employs five stages of which each has a powergain of 30. Determine the total gain of the amplifier in dB. | BTL 3 | Applying |
| 6. | Examine the nature of CMRR and mention various methods ofimproving CMRR. | BTL 4 | Analyzing |
| 7. | List the applications of differential amplifier. | BTL 1 | Remembering |
| 8. | CMRR of an amplifier is 100dB, calculate common mode gain , if thedifferential gain is 100. | BTL 1 | Remembering |
| 9. | Construct a Differential amplifier and write the ideal value of CMRR. | BTL 3 | Applying |
| 10. | Distinguish common mode and difference mode. | BTL 4 | Analyzing |
| 11. | Summarize the advantages and performance of class- C amplifier | BTL 2 | Understanding |
| 12. | Examine the impact of cross over distortion in an amplifier. | BTL 4 | Analyzing |
| 13. | Illustrate the ideal tuned circuit and write the expression for it’s resonantfrequency. | BTL 2 | Understanding |
| 14. | Enumerate the need of Complementary symmetry amplifiers. | BTL1 | Remembering |
| 15. | Assess the bootstrapping technique. | BTL5 | Evaluating |
| 16. | Outline the Conversion efficiency of power amplifier. | BTL 2 | Understanding |
| 17. | In an RC coupled power amplifier, the a.c. voltage across load RL= 100 Ω has a peak- to-peak value of 18V. Estimate the maximum possible a.c.load power. | BTL 6 | Creating |
| 18. | Quote the advantages of Push pull amplifier | BTL1 | Remembering |
| 19. | Enumerate the advantages of single tuned amplifiers. | BTL1 | Remembering |
| 20. | Outline the need for constant current source for difference amplifier. | BTL 2 | Understanding |
| **PART – B** |
| 1. | Illustrate the circuit of emitter coupled BJT differential amplifier, and derive expressions for differential gain, common mode gain and CMRR.(13) | BTL 2 | Understanding |
| 2. | 1. What is Neutralization? Explainany one method in brief. (8)
2. Tabulate the difference betweenvoltage and power amplifier. (5)
 | BTL 1 | Remembering |
| 3. | With neat sketch explain two stage cascaded amplifier and derive its overall Av, AI, RI and Ro. (13) | BTL 3 | Applying |
| 4. | Sketch he differential amplifier and its ac equivalent circuit. Derive for Ad and Ac. (13) | BTL 1 | Remembering |
| 5. | With neat diagram, explain the BJT differential amplifier with active load and derive Ad, Ac and CMRR. How CMRR can be improved? (13) | BTL 1 | Remembering |

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| 6. | 1. Explainthe different types of distortion in power amplifiers. (8)
2. In an ideal Class B amplifier with complimentary symmetry as shown in the figure, Vcc = 15V and RL =10 Ω. Determine the (a) maximum signal output power, the corresponding collector dissipation and conversion efficiency and (b) maximum dissipation on each transistor and the corresponding conversion efficiency. (5)

 | BTL 2 | Understanding |
| 7. | Develop the equation for differential mode gain and common mode gainof a differential amplifier using FET. Derive the expression for differential mode gain and common mode gain. (13) | BTL 3 | Applying |
| 8. | The differential amplifier has the following values RC = 50kΩ, RE= 100 kΩ and Rs = 10 kΩ. The transistor parameters are hie, = 50 kΩ, hfe = Vo = 2 x103, ro= 400kΩ.Determine Ad, Ac and CMRR in dB.(13) | BTL 5 | Evaluating |
| 9. | 1. Describe about complementary symmetry class B amplifier and obtain its efficiency. (7)
2. Outline the operation of class AB amplifier to avoid cross over distortion. (6)
 | BTL 1 | Remembering |
| 10. | The dual input balanced output differential amplifier having Rs=100Ω,RC =4.7kΩ, RE =6.8kΩ, hfe=100,Vcc=+15V, VEE=-15V. Find operating point values, differential &common mode gain, CMRR and output ifVs1=70mV(p-p)at 1 kHz and Vs2=40mV(p-p) . (13) | BTL 6 | Creating |
| 11. | If Class C tuned amplifier has RL = 6kΩ and required tank circuit Q = 80. Estimate the values of L & C of the tank circuit. Assume VCC=20V, resonant frequency = 5MHz and worst case power dissipation= 20mW. (13) | BTL 4 | Analyzing |
| 12. | 1. Draw a circuit diagram to show how the current in the output transistors of a power amplifier can be limited to a desired maximum level. Examine the circuit operation. (8)
2. Compare MOSFET to power BJT. (5)
 | BTL 4 | Analyzing |
| 13. | 1. Classify the power amplifiers and calculate the efficiency of each

types. (8)1. Discuss the advantages and disadvantages of any three classes of power amplifiers. (5)
 | BTL 2 | Understanding |
| 14. | Explain about Class A transformer coupled and Class C power amplifierand derive the expression for efficiency of the same. (13) | BTL 4 | Analyzing |
| **PART – C** |
| 1. | Evaluate the operating point, differential gain, common mode gain, CMRR and output voltage if VS1=70 mV peak to peak at 1kHz and VS2 =40mV peak to peak at 1kHz of dual input balanced outputdifferential amplifierhie=2.8kΩ. (15) | BTL 6 | Creating |

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| 2. | For the circuit shown below, calculate (i) Output power if the output voltage is 50 VPP (ii) Maximum ac output power (iii) DC input power if current drain is 0.5mA (iv) Efficiency if the current drain is 0.4mA and the output voltage is 30VPP. (v) Bandwidth of amplifier if Q=125(vi) Worst case transistor power dissipation. (15) | BTL 5 | Evaluating |
| 3. | A power transistor working in class-A operation is supplied from a 12- volt battery. If the maximum collector current change is 100 mA, Determine the power transferred to a 5Ω loudspeaker if it is : (15)1. directly connected in the collector
2. transformer-coupled for maximum power transference

Find the turn ratio of the transformer in the second case. | BTL 6 | Creating |
| 4. | Categorize the Neutralization methods used in an amplifier and assess itsnature of operation with an appropriate circuit diagram.Mention its advantages and disadvantages. (15) | BTL 5 | Evaluating |

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| **UNIT V - FEEDBACK AMPLIFIERS AND OSCILLATORS** |
| Advantages of negative feedback – voltage / current, series, Shunt feedback –positive feedback – Condition for oscillations, phase shift – Wien bridge, Hartley, Colpitts and Crystal oscillators. |
| **PART – A** |
| **Q. No** | **Questions** | **BT Level** | **Competence** |
| 1. | Examine the advantages of negative feedback. | BTL 4 | Analyzing |
| 2. | Summarize the disadvantages of negative feedback in amplifiers and how it can be overcome? | BTL 2 | Understanding |
| 3. | Discover how the amplifiers are classified according to the negative feedback? | BTL 3 | Applying |
| 4. | Show the equation for closed loop gain of series-shunt amplifier. | BTL 1 | Remembering |
| 5. | What type of feedback present in the circuit given below ? | BTL 1 | Remembering |

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| 6. | The open loop voltage gain of a transistor amplifier is liable to change by 30%. A feedback amplifier circuit with overall gain of 50 is to bedesigned. It is desired that overall gain should not vary by more than 1%. Determine the open loop gain and feedback factor. | BTL 5 | Evaluating |
| 7. | Predict the most commonly used feedback arrangement in cascadedamplifier and why? | BTL 2 | Understanding |
| 8. | Which type of feedback circuit increases gain of an amplifier? | BTL 1 | Remembering |
| 9. | Articulate your comments on the stability of feedback amplifiers. | BTL 3 | Applying |
| 10. | Illustrate the factors that affects the stability of amplifiers. | BTL 4 | Analyzing |
| 11. | Formulate the two Barkhausen conditions required for sinusoidaloscillation to be sustained. | BTL 6 | Creating |
| 12. | Compare oscillator and amplifier. | BTL 5 | Evaluating |
| 13. | Classify the types of feedback amplifiers and infer which type of feedbackis used in oscillators. | BTL 2 | Understanding |
| 14. | Write the expression for frequency of oscillation of RC phase shiftoscillator. | BTL 1 | Remembering |
| 15. | Choose the merits and demerits of RC phase shift oscillators. | BTL 1 | Remembering |
| 16. | Express the frequency of oscillations for a Wein bridge oscillator. | BTL 2 | Understanding |
| 17. | Select the advantages of a Colpitts Oscillator compared to a phase shiftoscillator. | BTL 3 | Applying |
| 18. | Draw the equivalent circuit of Crystal oscillator. | BTL 1 | Remembering |
| 19. | Outline the Piezo-electric effect. | BTL 4 | Analyzing |
| 20. | Compose the advantages of Crystal Oscillator. | BTL 6 | Creating |
| **PART - B** |
| 1. | 1. What is feedback? Show the difference betweenpositive and negative

feedback. Why negative feedback is very commonly used in many control and instrumentation circuits? (5)1. Write the effects of negative feedback on gain, bandwidth, noise and distortion of an amplifier circuit. How does it provide gain stability?

(8) | BTL 1 | Remembering |
| 2. | With a neat block diagram explain the operation of following feedback amplifiers.1. Voltage series feedback amplifier (7)
2. Current shunt feedback amplifier (6)
 | BTL 2 | Understanding |
| 3. | Demonstrate the following feedback configurations of amplifiers and obtain the feedback factor and closed loop gain.1. Shunt – Shunt feedback (6)
2. Series – Series feedback (7)
 | BTL 3 | Applying |

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| 4. | 1. The open loop voltage gain of an amplifier is 50 and its input impedance is 1kΩ. Estimate the input impedance, when a negative feedback of 10% is applied to the amplifier? (5)
2. Evaluate the voltage gain, input and output resistance of a voltage series feedback amplifier having 𝐴𝑣 = 300, 𝑅𝑖 = 1.5𝑘Ω, 𝑅 = 50𝑘Ω 𝑎𝑛𝑑 𝛽 = 1 . (8)

15 | BTL 5 | Evaluating |
| 5. | Identify the nature of feedback for the given circuit diagram. Let𝑅𝑐1 = 3𝐾Ω, 𝑅𝑐2 = 500Ω, 𝑅𝐸 = 50Ω, 𝑅𝑠 = 𝑅𝑓 = 1.2𝑘Ω, ℎ𝑓𝑒 =50, ℎ𝑖𝑒 = 1.1𝑘Ω, ℎ𝑟𝑒 = ℎ𝑐𝑒 = 0. Find overall voltage gain 𝐴𝑣 , overall current gain 𝐴𝑖𝑓 , input impedance 𝑅𝑖𝑓 and output impedance 𝑅𝑜𝑓 . (13) | BTL 1 | Remembering |
| 6. | 1. Point out the advantages of negative current feedback on the

performance of amplifiers. (4)1. When a negative voltage feedback is applied to an amplifier of gain 100, the overall gain falls to 50 analyze the fraction of the output voltage feedback. If this fraction is maintained, examine the value of the amplifier gain required if the overall stage gain is to be 75.

(4)1. Classify the various types of topology in feedback amplifiers. (5)
 | BTL 4 | Analyzing |
| 7. | 1. Illustrate about the stability analysis using the frequency response of the loop gain of the feedback amplifier system. (6)
2. Choose the compensation methods to achieve stability in

amplifiers. (7) | BTL 3 | Applying |
| 8. | Explain the RC phase shift oscillator with a neat diagram by using BJTand also derive the condition for oscillation. (13) | BTL 2 | Understanding |
| 9. | With neat diagram examine the Wein bridge oscillator and derive anexpression for frequency of oscillation. (13) | BTL 4 | Analyzing |
| 10. | Write the expressions for frequency of oscillation for Hartley oscillatorwith a neat circuit diagram by using BJT and briefly explain it. (13) | BTL 1 | Remembering |
| 11. | Describe the operation of Colpitts oscillator with neat circuit diagram.Also derive the expressions for the frequency of oscillation and the conditin for maintenance of oscillation. (13) | BTL 2 | Understanding |
| 12. | (i) In a Colpitts oscillator, 𝐶1 = 𝐶2 = 𝐶 𝑎𝑛𝑑 𝐿 = 100 × 10−6𝐻. The frequency of oscillation is500𝑘𝐻𝑧. Design the value of 𝐶. (6)1. In Colpitts oscillator, the desired frequency is 500𝑘𝐻𝑧. Estimate the value of 𝐿 by assuming 𝐶 = 1000𝑝𝐹. (4)
2. A 1 mH inductor is available. Choose the capacitor values in a Colpitts oscillator so that f = l MHz and feedback fraction is 0.25

(3) | BTL 6 | Creating |

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| 13. | Examine the operation of the Crystal oscillators. (13) | BTL 1 | Remembering |
| 14. | 1. A crystal has the following parameters L = 0.5 H, Cs = 0.06 pF,

Cp = 1pF and R = 5kΩ. Inspect the series and parallel resonant frequencies and Q-factor of the crystal. (8)1. Distinguish between Crystal oscillators & LC oscillators. (5)
 | BTL 4 | Analyzing |
| **PART – C** |
| 1. | When a portion of the output signal is fed to input, as you are aware, feedback is generated. Developthe difference betweennegative feedback and positive feedback and elaborate on their individual advantages. How different parameters of an amplifier will be affected by these two typesof feedback? (15) | BTL 6 | Creating |
| 2. | Sketchthe circuit diagram of a two-stage capacitorcoupled BJT amplifierthat uses series voltage negative feedback. Briefly explain how thefeedback operates. (15) | BTL 5 | Evaluating |
| 3. | Design an oscillator to operate at a frequency of 10kHz which gives an extremely pure sine wave output, good frequency stability and highly stabilized amplitude. Discuss the operation of this oscillator as an audiosignal generators. (15) | BTL 6 | Creating |
| 4. | 1. Determine the RC Phase shift oscillator to generate 5 kHz sine wave with 20V peak to peak amplitude and draw the circuit for designed by assuming *hfe* = 150. (10)
2. A Wein bridge oscillator has a frequency of 6000 Hz. If 𝑅1 = 𝑅2 =

100𝑘Ω . Select the value of 𝐶1 𝑛𝑑 𝐶2. (5) | BTL 5 | Evaluating |